

ABSTRACT OF THE DISCLOSURE

Disclosed herein is a via hole dry etching method using an organic SOG film as an interlayer dielectric having low-K. In the dry etching method, a mixed gas containing at least C₄F₈ and O₂ is used as an etching gas and an O₂/(C₄F₈+O₂) mixture ratio is set to 50% or less, thereby to carry out via hole dry etching. Further, the via hole dry etching is carried out by using a mixed gas containing at least CF₄, CHF₃ and N₂ and setting the quantity of flow of N₂ to above 10% and below 80% of the quantity of flow of CF₄+CHF₃+N₂.